

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0117I uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =100V,I_D =17A

 $R_{DS(ON)} < 70 \text{m}\Omega$ @ $V_{GS}=10V$ (Typ:56m Ω)

 $R_{DS(ON)} < 85m\Omega$ @ V_{GS} =4.5V (Typ:65m Ω)

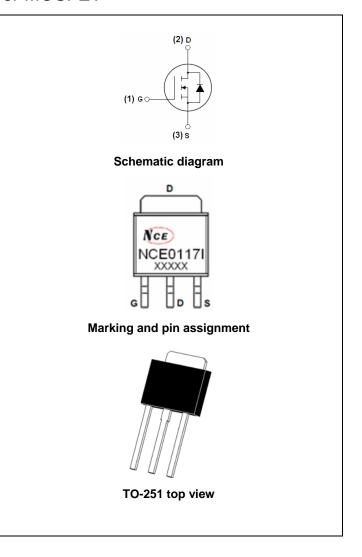
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0117I	NCE0117I	TO-251	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	17	А
Drain Current-Continuous(T _C =100°C)	I _D (100°ℂ)	12	А
Pulsed Drain Current	I _{DM}	60	А
Maximum Power Dissipation	P _D	55	W
Single pulse avalanche energy (Note 5)	E _{AS}	28	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}\!\mathbb{C}$





Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	2.27	°C/W	1
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	110	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	<u>.</u>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.8	2.5	V	
Danier Courses On Otata Basistana	-	V _{GS} =10V, I _D =5A	-	56	70	0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =3A		65	85	mΩ	
Forward Transconductance	g FS	V _{DS} =5V,I _D =5A	12	-	-	S	
Dynamic Characteristics (Note4)				ı			
Input Capacitance	C _{lss})/ 05\/\/ 0\/	-	1350	-	PF	
Output Capacitance	C _{oss}	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	-	240	-	- V 1 μA 100 nA 2.5 V 70 mΩ 85 - S - PF - PF - PF - nS - nS - nS - nC - nC - nC - nC - nC	
Reverse Transfer Capacitance	C _{rss}		PF				
Switching Characteristics (Note 4)			•				
Turn-on Delay Time	t _{d(on)}		-	13.8	-	nS	
Turn-on Rise Time	t _r	V_{DD} =30 V , R_L =15 Ω	-	9.3	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =2.5 Ω	-	43.8	-	nS	
Turn-Off Fall Time	t _f		-	11.4	-	nS	
Total Gate Charge	Qg	\/ 20\/ L 5A	-	30		nC	
Gate-Source Charge	Q _{gs}		-	6.4	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	8.6	-	nC	
Drain-Source Diode Characteristics			•				
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =17A	-	-	1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	17	Α	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is neg	ligible (turi	n-on is do	minated b	y LS+LD)	

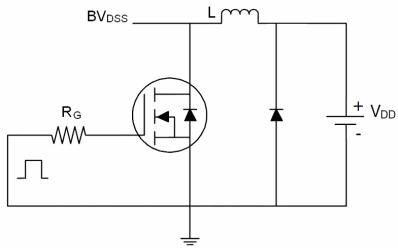
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

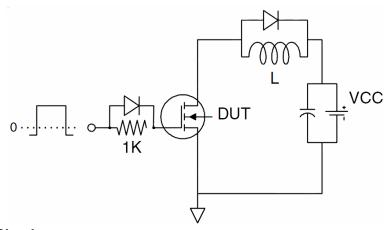


Test Circuit

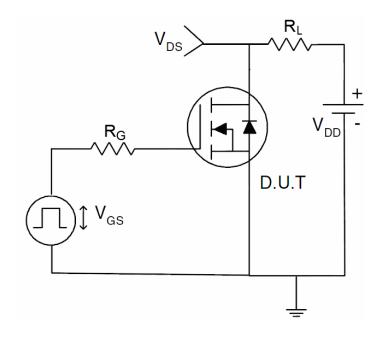
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

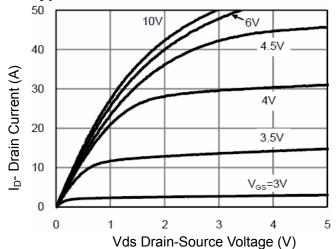


Figure 1 Output Characteristics

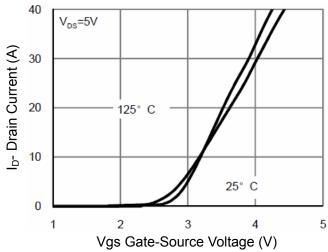


Figure 2 Transfer Characteristics

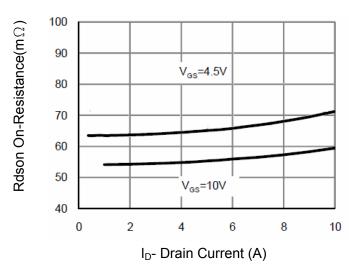


Figure 3 Rdson- Drain Current

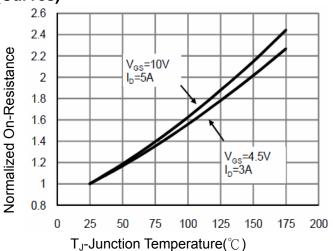


Figure 4 Rdson-JunctionTemperature

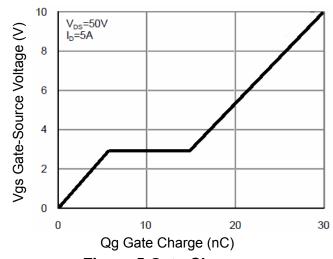


Figure 5 Gate Charge

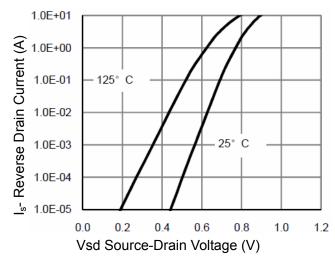


Figure 6 Source- Drain Diode Forward



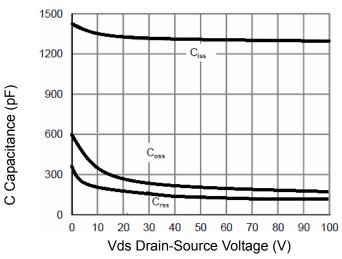


Figure 7 Capacitance vs Vds

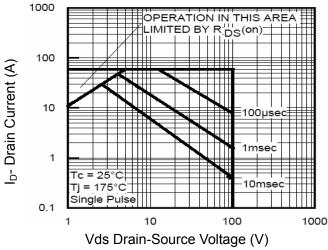


Figure 8 Safe Operation Area

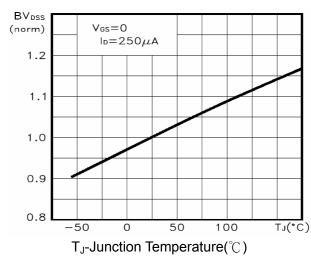


Figure 9 BV_{DSS} vs Junction Temperature

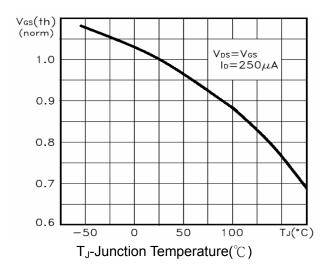


Figure 10 V_{GS(th)} vs Junction Temperature

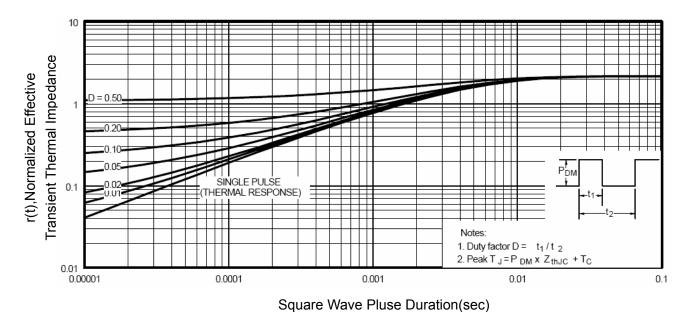
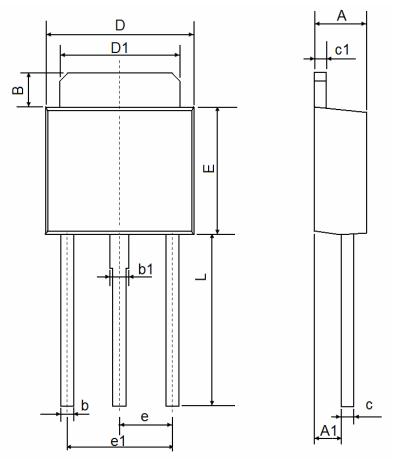


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-251 Package Information



Combal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	1.050	1.350	0.042	0.054	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.430	0.580	0.017	0.023	
c1	0.430	0.580	0.017	0.023	
D	6.350	6.650	0.250	0.262	
D1	5.200	5.400	0.205	0.213	
E	5.400	5.700	0.213	0.224	
е	2.300 TYP.		0.091 TYP.		
e1	4.500	4.700	0.177	0.185	
L	7.500	7.900	0.295	0.311	







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